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SHARP S22MD1V/S22MD3

S22MD1V/S22MD3

Photothyristor Coupler

* Lead forming type (I type) and taping reel type (P type) of S22MD1V are also available (S22MD1VI/S22MD1P)

** TÜV (DIN-VDE0884) approved type is also available as an option.

■ Features

1. High repetitive peak OFF-state voltage

 $(V_{DRM} : MIN. 600V)$ 2. Low trigger current

(I_{FT}: MAX. 10mA at $R_G = 20k\Omega$)

3. High isolation voltage between input and output

S22MD1V ••• V_{iso} : 5 000 V_{rms} **S22MD3V** ••• V_{iso} : 2 500 V_{rms}

S22MD1V and **S22MD3** are for 200V line.

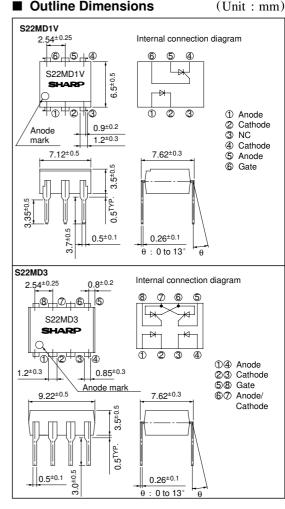
4. Recognized by UL, file NO. 64380

■ Applications

1. ON-OFF operation for a low power load

2. For triggering high power thyristor and triac

Outline Dimensions



■ Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Parameter		Cramb ol	Rating		Unit	
		Symbol	S22MD1V	S22MD3	Unit	
Input	Forward current	I_F	50		mA	
	Reverse voltage	V _R	6		V	
Output	RMS ON-state current	I_T	200		mA _{rms}	
	*1Peak one cycle surge current	I surge	2		A	
	*2Repetitive peak OFF-state voltage	V_{DRM}	600		V	
	*2Repetitive peak reverse voltage	V _{RRM}	600	-	V	
*3Isolation voltage		V _{iso}	5 000	2 500	V_{rms}	
Operating temperature		T _{opr}	-30 to +100	-30 to +100	°C	
Storage temperature		T stg	-55 to +125	-40 to +125	°C	
*4Soldering temperature		T _{sol}	260		°C	

^{*1 50}H z, sine wave

■ Electro-optical Characteristics

(Ta= 25°C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input	Forward voltage		$V_{\rm F}$	$I_F = 30mA$	-	1.2	1.4	V
	Reverse current		I_R	$V_R = 3V$	-	-	10-5	A
Output	Repetitive peak OFF-state curren	t	I_{DRM}	$V_{DRM} = Rated, R_G = 20k\Omega$	-	-	10-6	A
	*5Repetitive peak reverse current		I_{RRM}	$V_{RRM} = Rated, R_G = 20k\Omega$	-	-	10-6	A
	ON-state voltage		V _T	$I_T = 200 \text{mA}$	-	1.0	1.4	V
	Holding current		I_{H}	$V_D = 6V$, $R_G = 20k\Omega$	-	0.2	1	mA
	Critical rate of	S22MD1V	dV/dt	$V_{DRM} = 1/\sqrt{2}$ Rated, $R_G = 20k\Omega$	5	-	-	V/μs
	rise of OFF-state voltage	S22MD3	a v/ai		3	-	-	
Transfer	Minimum trigger current		I_{FT}	$V_{\rm D}$ = 6V, $R_{\rm L}$ = 100Ω , $R_{\rm G}$ = $20k\Omega$	-	-	10	mA
charac-	Isolation resistance		R _{ISO}	DC500V, 40 to 60% RH	5 x 10 ¹⁰	1011	-	Ω
teristics	Turn-on time		t on	V_D = 6V, R $_G$ = 20k Ω , R $_L$ = 100 Ω , I $_F$ = 30mA	_	20	50	μs

^{*5} Applies only to S22MD1V

 $^{*2} R_G = 20k\Omega$

^{*3 40} to 60% RH, AC for 1 minute

^{*4} For 10 seconds

Fig. 1 RMS ON-state Current vs.
Ambient Temperature

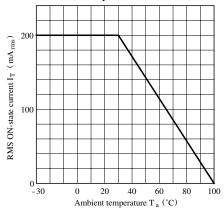


Fig. 3 Forward Current vs. Forward Voltage

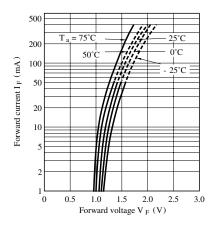


Fig. 5 Minimum Trigger Current vs.

Gate Resistance

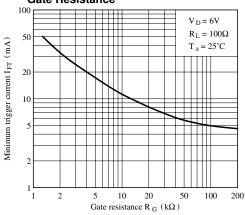


Fig. 2 Forward Current vs.
Ambient Temperature

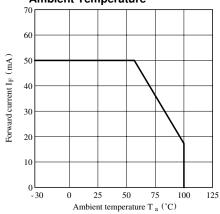


Fig. 4 Minimum Trigger Current vs.
Ambient Temperature

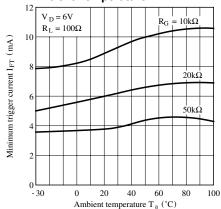


Fig. 6 Break Over Voltage vs. Ambient Temperature

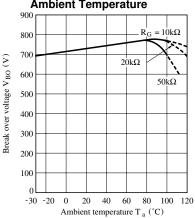


Fig. 7 Critical Rate of Rise of OFF-state Voltage vs. Ambient Temperature

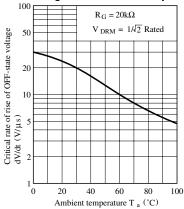


Fig. 9 Repetitive Peak OFF-state Current vs. Ambient Temperature

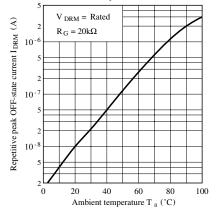
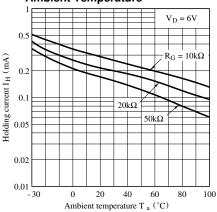


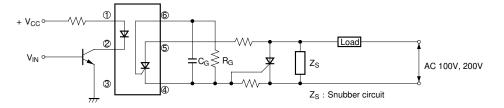
Fig. 8 Holding Current vs.
Ambient Temperature



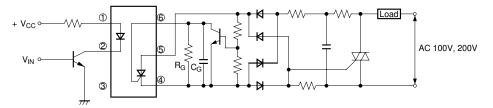
■ Basic Operation Circuit

● S22MD1V

Medium/High Power Thyristor Drive Circuit

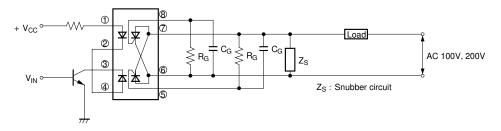


Medium/High Power Triac Drive Circuit (Zero-cross Operation)

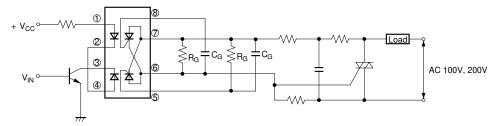


● S22MD3

Low Power Load Drive Circuit



Medium/High Power Triac Drive Circuit



• Please refer to the chapter "Precautions for Use" (Page 78 to 93).

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- Alarm equipment
- Various safety devices, etc.
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